Circular Beam Low Operating Current



ODE-208-1437D (Z)

Rev.4 Mar. 2005

Description

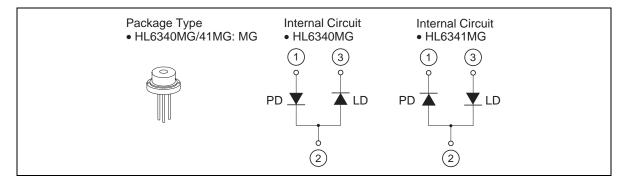
The HL6340MG/41MG are 0.63 μ m band AlGaInP laser diodes can be operated with low operating current. These products were designed by self aligned refractive index (SRI) active layer structure. These are suitable as a light source for laser levelers, laser scanners and optical equipment for measurement.

Application

- Laser leveler
- Laser scanner
- Measurement

Features

- Optical output power : 5 mW CW
- Single longitudinal mode
- Visible light power : 635 nm Typ
- Low operating current : 25 mA Typ
- Low aspect ratio : 1.2 Typ
- Operating temperature :+50°C
- TM mode oscillation





Absolute Maximum Ratings

 $(T_{C} = 25^{\circ}C)$

ltem	Symbol	Value	Unit
Optical output power	Po	5	mW
Pulse optical output power	$P_{O(Pulse)}$	6 *	mW
LD reverse voltage	V _{R(LD)}	2	V
PD reverse voltage	V _{R(PD)}	30	V
Operating temperature	Topr	–10 to +50	C°
Storage temperature	Tstg	-40 to +85	°C

Note: Pulse condition : Pulse width $\leq 1 \ \mu$ s, duty = 50%

Optical and Electrical Characteristics

$(T_{C} = 25^{\circ}C)$

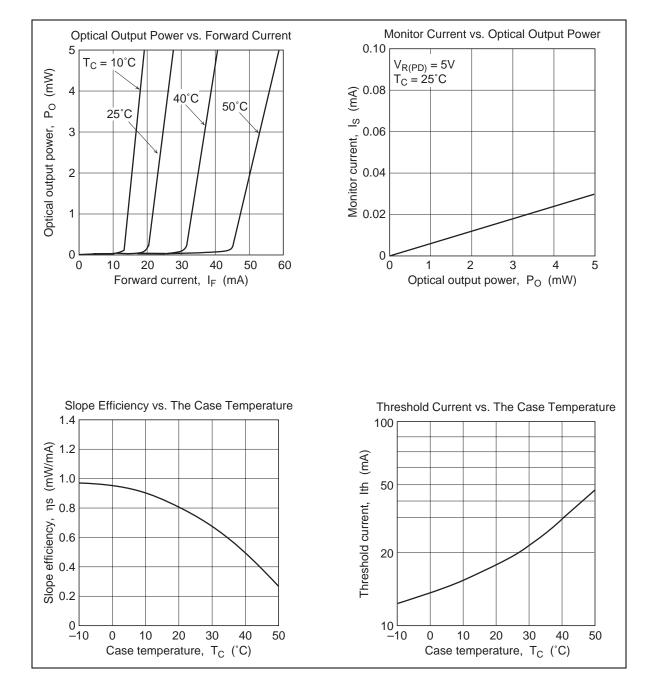
Item	Symbol	Min	Тур	Max	Unit	Test Condition
Optical output power	Po	5	_	_	mW	_
Threshold current	lth	_	20	30	mA	_
Slope efficiency	ηs	0.5	0.8	1.1	mW/mA	$3 \text{ (mW) / } (I_{(4mW)} - I_{(1mW)})$
Operating current	I _{OP}	—	25	40	mA	P ₀ = 5 mW
Operating voltage	V _{OP}	—	2.4	2.7	V	P ₀ = 5 mW
Lasing wavelength	λρ	630	635	640	nm	P ₀ = 5 mW
Beam divergence parallel to the junction	θ//	13	17	25	deg.	P _o = 5 mW
Beam divergence perpendicular to the junction	θ⊥	16	20	25	deg.	P _o = 5 mW
Aspect ratio	θ⊥/θ//	_	1.2	1.5	_	P ₀ = 5 mW
Monitor current	ls	0.01	0.03	0.06	mA	P_0 = 5 mW, $V_{R(PD)}$ = 5 V

Notes: 1. Care must be taken in laser diodes handling to prevent optical damage caused by forward surges as well as by ESD.

2. The wavefront performance is not guaranteed.

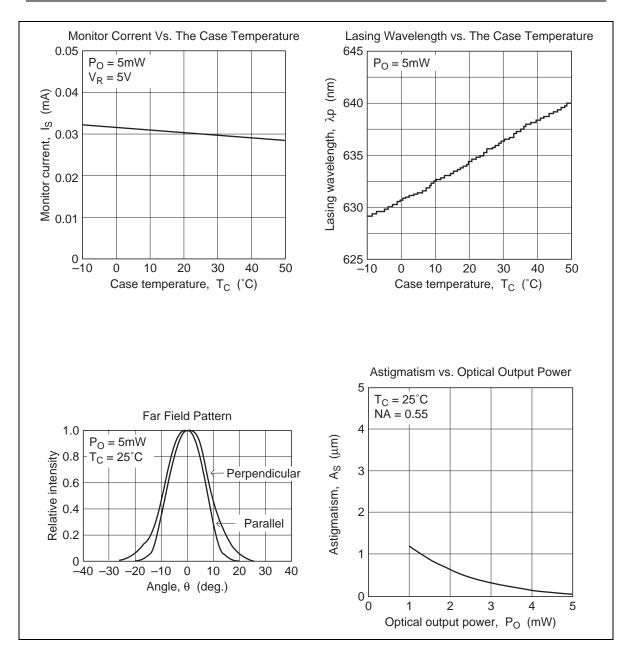
3. The beam has 12 deg offset against the package reference plane. Please take account it mounted on a board.



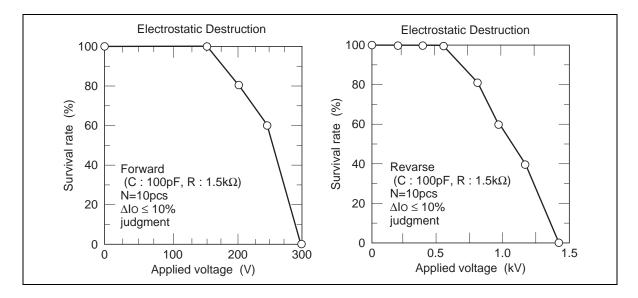


Typical Characteristic Curves



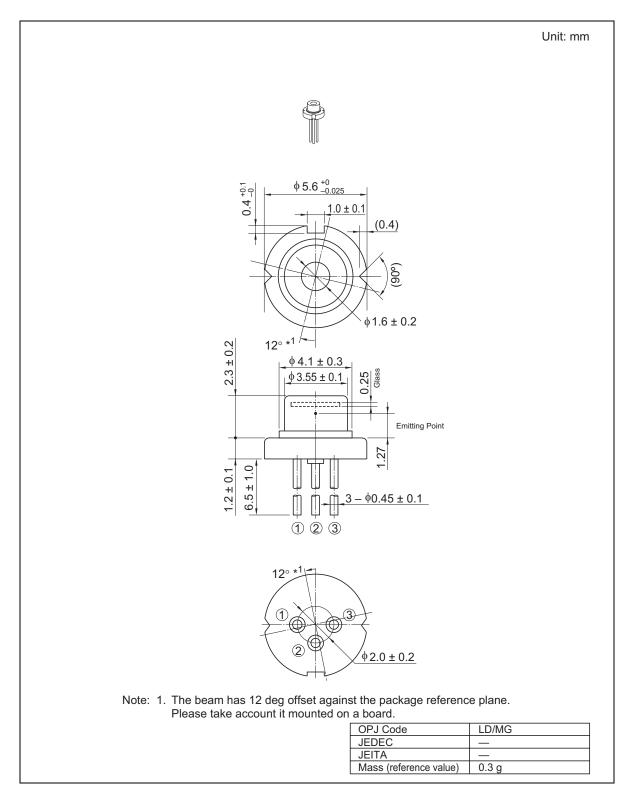








Package Dimensions

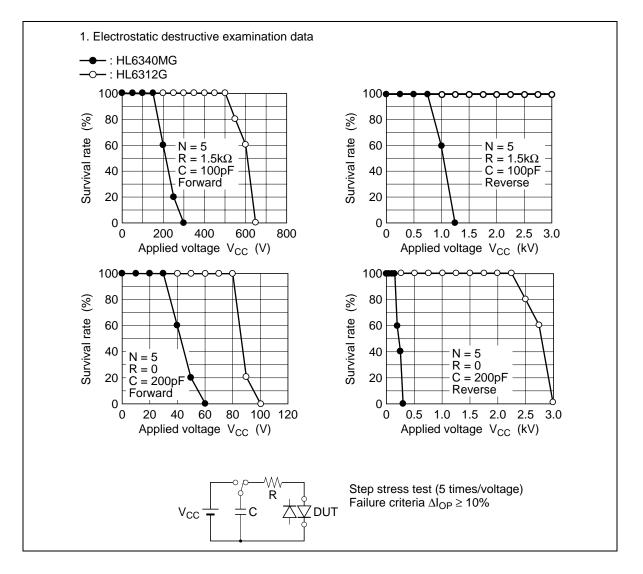


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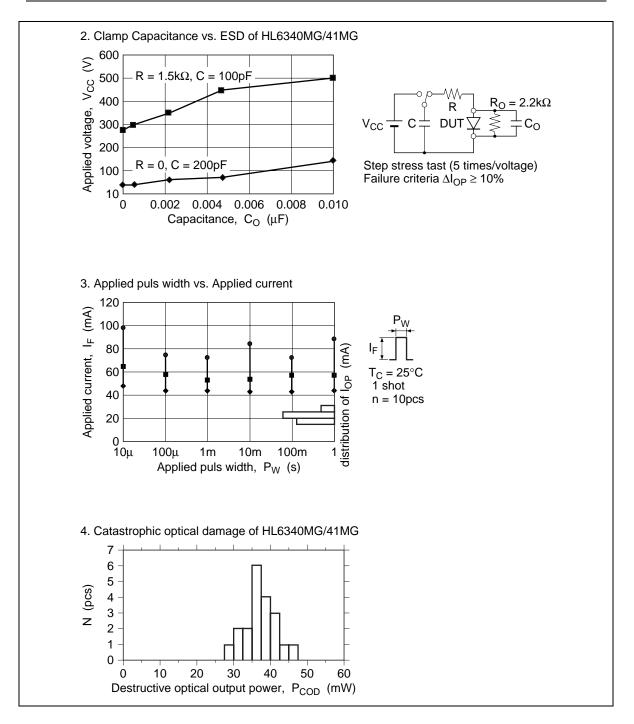


The Cautions on the Handing of HL6340MG/41MG

As laser diode differ from silicon devices, the area of safe operation (ASO) of laser diodes is not decided by power consumption alone, but optical output must be considered from view point of optical damage. These products are more sensitive to static electricity or an surge current than the conventional product. The following is test data of ESD (electric static damage). The operating condition should be within 5 mW and the working please should be keep small static electricity level such as 20 V less and small surge current such as 40 mA less from out.









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